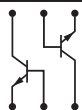


CMKT2222A

**SURFACE MOUNT
DUAL NPN SMALL SIGNAL
SILICON SWITCHING
TRANSISTORS**

ULTRAmTM



SOT-363 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKT2222A consists of two individually isolated 2222A NPN silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-363 surface mount package. This ULTRAmTM device has been designed for small signal general purpose and switching applications.

MARKING CODE: K22

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO}	75
V_{CEO}	40
V_{EBO}	6.0
I_C	600
P_D	350
T_J, T_{stg}	-65 to +150
θ_{JA}	357

UNITS

V
V
V
mA
mW
$^{\circ}\text{C}$
$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=60\text{V}$		10	nA
I_{CBO}	$V_{CB}=60\text{V}, T_A=125^{\circ}\text{C}$		10	μA
I_{CEV}	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$		10	nA
I_{EBO}	$V_{EB}=3.0\text{V}$		10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	75		V
BV_{CEO}	$I_C=10\text{mA}$	40		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	35		
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	50		
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	40		
f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	300		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		25	pF

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CMKT2222A

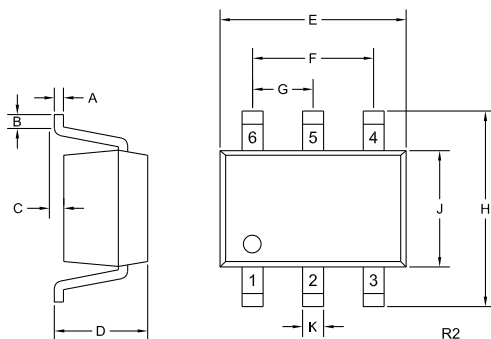
**SURFACE MOUNT
DUAL NPN SMALL SIGNAL
SILICON SWITCHING
TRANSISTORS**



ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$)

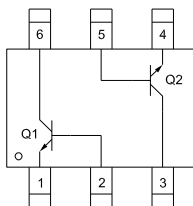
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{ie}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	2.0	8.0	$k\Omega$
h_{ie}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=1.0\text{kHz}$	0.25	1.25	$k\Omega$
h_{re}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$		8.0	$\times 10^{-4}$
h_{re}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=1.0\text{kHz}$		4.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	50	300	
h_{fe}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=1.0\text{kHz}$	75	375	
h_{oe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	5.0	35	μS
h_{oe}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=1.0\text{kHz}$	25	200	μS
r_b/C_C	$V_{CB}=10\text{V}$, $I_E=20\text{mA}$, $f=31.8\text{MHz}$		150	ps
NF	$V_{CE}=10\text{V}$, $I_C=100\mu\text{A}$, $R_S=1.0k\Omega$, $f=1.0\text{kHz}$		4.0	dB
t_d	$V_{CC}=30\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$		10	ns
t_r	$V_{CC}=30\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$		25	ns
t_s	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$		225	ns
t_f	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$		60	ns

SOT-363 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)



LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: K22

R4 (13-January 2010)